

ABSTRACT OF THE DISCLOSURE

A structure of protection of an area of a semiconductor wafer including a lightly-doped substrate of a first conductivity type against high-frequency noise likely to be injected from components formed in the upper portion of a second area of the wafer. The structure includes a very heavily-doped wall of the first conductivity type having substantially the depth of the upper portion. The wall is divided into segments, each of which is connected to a ground plane.

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